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Application Serial No. 10/611,307
Responsive to the Office Action Mailed: September 13, 2007

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1-14. (Cancelled)

15. (Twice Amended) A semiconductor device comprising:

a substrate,

a multilayer formed on the substrate, the multilayer

comprising a plurality of semiconductor elements and a plurality of dummy semiconductor elements, and

a semiconductor element area on the substrate, which includes the plurality of semiconductor elements, the semiconductor element area being surrounded by the plurality of dummy semiconductor elements,

wherein each of the plurality of semiconductor elements includes a capacitor which is comprised of a bottom electrode, a first dielectric layer on the bottom electrode and a top electrode on the first dielectric layer, and the first dielectric layer is composed of a material selected from a dielectric material having a dielectric constant of 100 or more and a ferroelectric material,

wherein each of the plurality of dummy semiconductor elements includes a dummy capacitor which is comprised of a dummy bottom electrode, a second dielectric layer on the dummy bottom electrode and a dummy top electrode on the second dielectric layer, and the second dielectric layer is composed of a material selected from a dielectric material having a dielectric constant of 100 or more and a ferroelectric material,

wherein each of the plurality of dummy semiconductor elements is located so that a space between the electrode and the dummy electrode is in a predetermined range, and

wherein the multilayer is produced by a method comprising:

forming a dielectric film for the first dielectric layer and the second dielectric layer;

forming an electrically conductive film on the dielectric film;

[[and]]

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etching the electrically conductive film so as to form the electrode and the dummy electrode, and wherein each of the plurality of semiconductor elements and each of the plurality of dummy semiconductor elements have the same dimensions.

16. (Previously Presented) A semiconductor device according to claim 15, wherein the predetermined range of the space is between 0.3 μ m and 14 μ m.

17. (Previously Presented) A semiconductor device according to claim 15, wherein remnant polarization in the capacitor is in the range of 13 to 15 μ C/cm².

18. (Previously Presented) A semiconductor device according to claim 15, wherein the first dielectric layer and the second dielectric layer are composed of a material selected from SrBi_xTa_xO_y, Ba_xSr_{1-x}TiO_x, Pb(Zr_{1-x}Ti_x)O₃, SrBi₂(Ta_{1-x}Nb_x)₂O₉ or Bi₄Ti₃O₁₂, where 0 \leq x \leq 1.